



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

DMBTA55

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

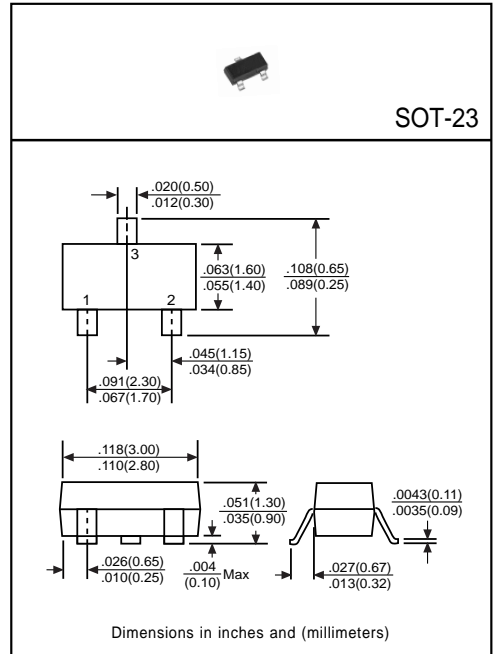
Designed for general purpose amplifier applications.

Pinning

- 1 = Base
- 2 = Emitter
- 3 = Collector

Absolute Maximum Ratings($T_A=25^{\circ}C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-4	V
Collector Current	I_C	-500	mA
Total Power Dissipation	P_D	225	mW
Junction Temperature	T_J	+150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}C$



Electrical Characteristics

(Ratings at $25^{\circ}C$ ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-60	-	-	V	$I_C=-100\mu A$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-60	-	-	V	$I_C=-1mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	-4	-	-	V	$I_E=-100\mu A$
Collector Cutoff Current	I_{CBO}	-	-	-100	nA	$V_{CB}=-60V$
	I_{CEO}	-	-	-100	nA	$V_{CE}=-50V$
Collector-Emitter Saturation Voltage ⁽¹⁾	$V_{CE(sat)}$	-	-	-0.25	V	$I_C=-100mA, I_B=-10mA$
Base-Emitter On Voltage	$V_{BE(on)}$	-	-	-1.2	V	$I_C=-100mA, V_{CE}=-1V$
DC Current Gain ⁽¹⁾	h_{FE1}	80	-	250	-	$I_C=-10mA, V_{CE}=-1V$
	h_{FE2}	80	-	-	-	$I_C=-100mA, V_{CE}=-1V$
Transition Frequency	f_T	50	-	-	MHz	$I_C=-100mA, V_{CE}=-1V$

(1) Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$